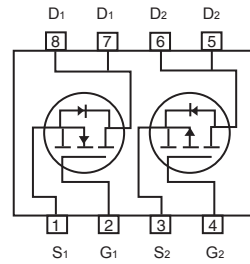
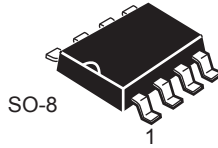


Dual Enhancement Mode Field Effect Transistor (N and P Channel)

PRELIMINARY

FEATURES

- 60V, 4.5A, $R_{DS(ON)} = 55m\Omega$ @ $V_{GS} = 10V$.
 $R_{DS(ON)} = 72m\Omega$ @ $V_{GS} = 4.5V$.
- -60V, -3.1A, $R_{DS(ON)} = 130m\Omega$ @ $V_{GS} = -10V$.
 $R_{DS(ON)} = 170m\Omega$ @ $V_{GS} = -4.5V$.
- Super high dense cell design for extremely low $R_{DS(ON)}$.
- High power and current handing capability.
- RoHS compliant.
- Surface mount Package.



ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ C$ unless otherwise noted

Parameter	Symbol	N-Channel	P-Channel	Units
Drain-Source Voltage	V_{DS}	60	-60	V
Gate-Source Voltage	V_{GS}	± 20	± 20	V
Drain Current-Continuous	I_D	4.5	-3.1	A
Drain Current-Pulsed ^a	I_{DM}	18	-12.4	A
Maximum Power Dissipation	P_D	2.0		W
Operating and Store Temperature Range	T_J, T_{stg}	-55 to 150		$^\circ C$

Thermal Characteristics

Parameter	Symbol	Limit	Units
Thermal Resistance, Junction-to-Ambient ^b	$R_{\theta JA}$	62.5	$^\circ C/W$

N-Channel Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 60V, V_{GS} = 0V$			1	μA
Gate Body Leakage Current, Forward	I_{GSSF}	$V_{GS} = 20V, V_{DS} = 0V$			100	μA
Gate Body Leakage Current, Reverse	I_{GSSR}	$V_{GS} = -20V, V_{DS} = 0V$			-100	μA
On Characteristics ^c						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	1		3	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 4.5A$		44	55	$m\Omega$
		$V_{GS} = 4.5V, I_D = 4A$		52.5	72	$m\Omega$
Dynamic Characteristics ^d						
Input Capacitance	C_{iss}	$V_{DS} = 25V, V_{GS} = 0V,$ $f = 1.0\text{ MHz}$		550		pF
Output Capacitance	C_{oss}			65		pF
Reverse Transfer Capacitance	C_{rss}			40		pF
Switching Characteristics ^d						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 30V, I_D = 1A,$ $V_{GS} = 10V, R_{GEN} = 6\Omega$		9		ns
Turn-On Rise Time	t_r			4		ns
Turn-Off Delay Time	$t_{d(off)}$			28		ns
Turn-Off Fall Time	t_f			3		ns
Total Gate Charge	Q_g	$V_{DS} = 30V, I_D = 4.5A,$ $V_{GS} = 10V$		13		nC
Gate-Source Charge	Q_{gs}			1		nC
Gate-Drain Charge	Q_{gd}			3		nC
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Current ^b	I_S				1	A
Drain-Source Diode Forward Voltage ^c	V_{SD}	$V_{GS} = 0V, I_S = 1.5A$			1.2	V
Notes : <input type="checkbox"/> a.Repetitive Rating : Pulse width limited by maximum junction temperature. <input type="checkbox"/> b.Surface Mounted on FR4 Board, $t \leq 10\text{ sec.}$ <input type="checkbox"/> c.Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$. <input type="checkbox"/> d.Guaranteed by design, not subject to production testing. <input type="checkbox"/> <input type="checkbox"/>						

P-Channel Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = -250\mu A$	-60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -60V, V_{GS} = 0V$			-1	μA
Gate Body Leakage Current, Forward	I_{GSSF}	$V_{GS} = 20V, V_{DS} = 0V$			100	nA
Gate Body Leakage Current, Reverse	I_{GSSR}	$V_{GS} = -20V, V_{DS} = 0V$			-100	nA
On Characteristics^b						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = -250\mu A$	-1		-3	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -3.1A$		100	130	$m\Omega$
		$V_{GS} = -4.5V, I_D = -2.8A$		130	170	$m\Omega$
Dynamic Characteristics^c						
Input Capacitance	C_{iss}	$V_{DS} = -30V, V_{GS} = 0V,$ $f = 1.0\text{ MHz}$		645		pF
Output Capacitance	C_{oss}			65		pF
Reverse Transfer Capacitance	C_{rss}			40		pF
Switching Characteristics^c						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -30V, I_D = -1A,$ $V_{GS} = -10V, R_{GEN} = 6\Omega$		12		ns
Turn-On Rise Time	t_r			4		ns
Turn-Off Delay Time	$t_{d(off)}$			30		ns
Turn-Off Fall Time	t_f			4		ns
Total Gate Charge	Q_g	$V_{DS} = -30V, I_D = -3.1A,$ $V_{GS} = -10V$		12		nC
Gate-Source Charge	Q_{gs}			1.8		nC
Gate-Drain Charge	Q_{gd}			2.5		nC
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Current	I_S				-1	A
Drain-Source Diode Forward Voltage ^b	V_{SD}	$V_{GS} = 0V, I_S = -1.0A$			-1.2	V
Notes : □ a.Repetitive Rating : Pulse width limited by maximum junction temperature. b.Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$. □ c.Guaranteed by design, not subject to production testing. □						

N-CHANNEL

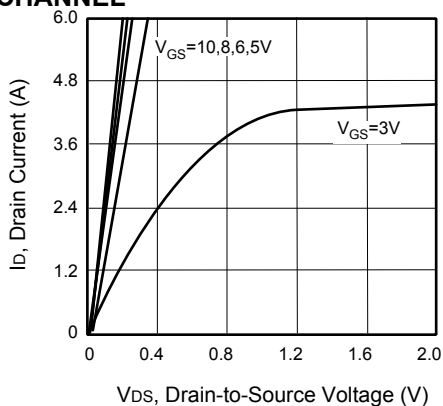


Figure 1. Output Characteristics

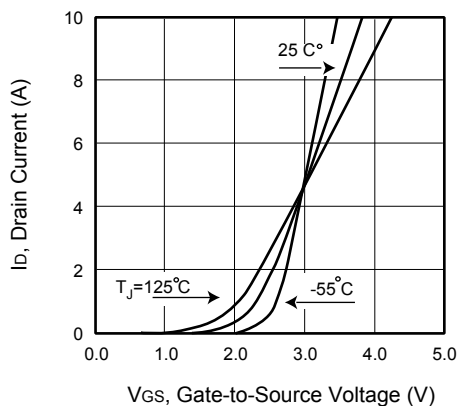


Figure 2. Transfer Characteristics

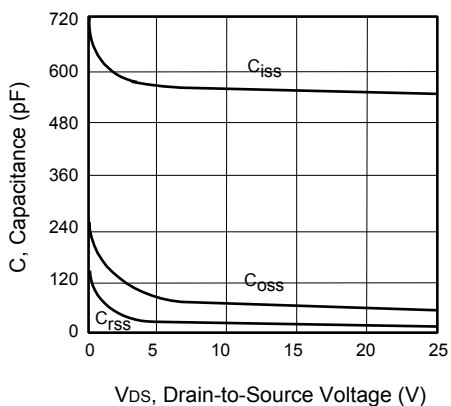


Figure 3. Capacitance

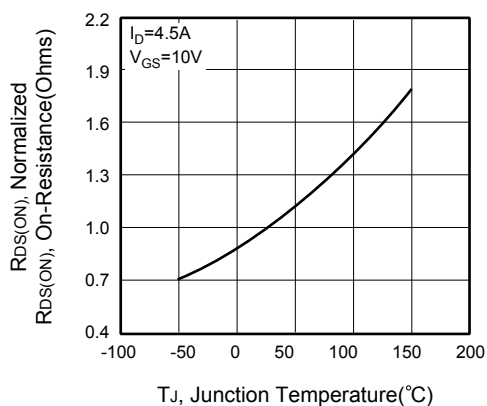


Figure 4. On-Resistance Variation with Temperature

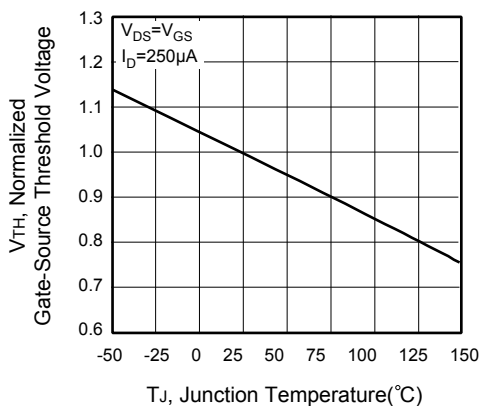


Figure 5. Gate Threshold Variation with Temperature

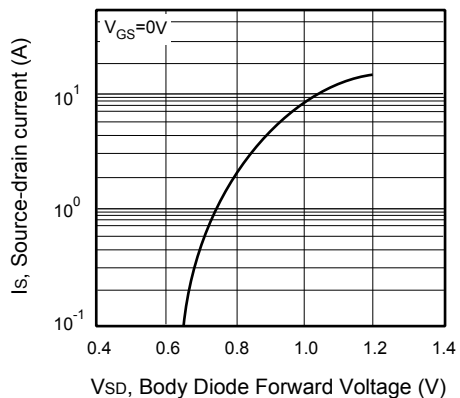


Figure 6. Body Diode Forward Voltage Variation with Source Current

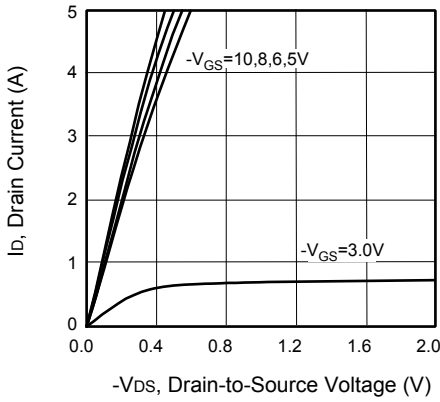


Figure 7. Output Characteristics

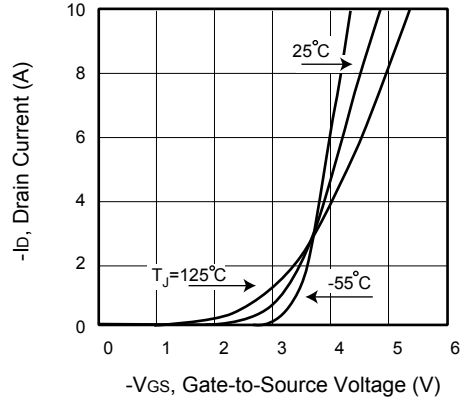


Figure 8. Transfer Characteristics

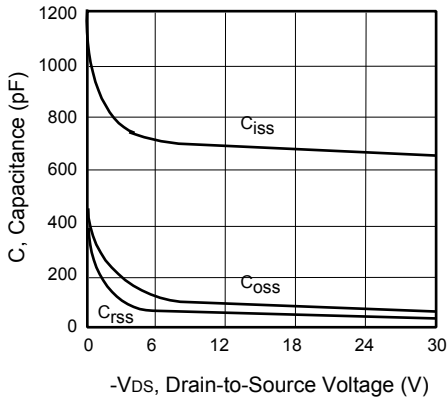


Figure 9. Capacitance

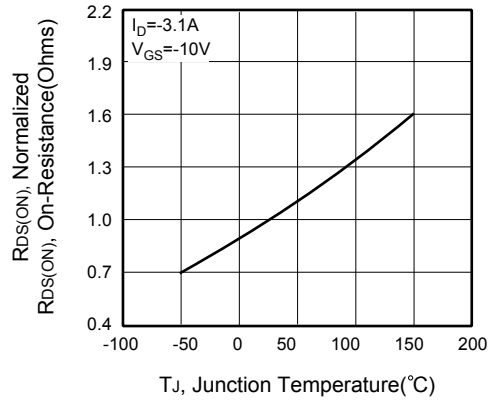


Figure 10. On-Resistance Variation with Temperature

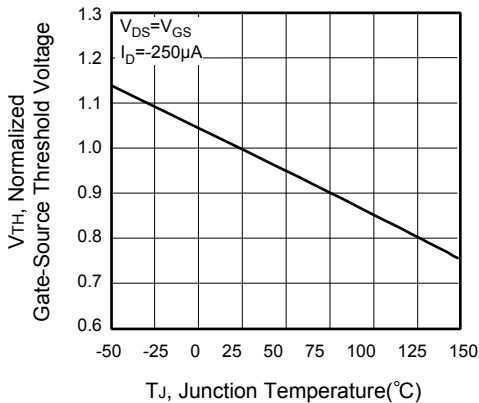


Figure 11. Gate Threshold Variation with Temperature

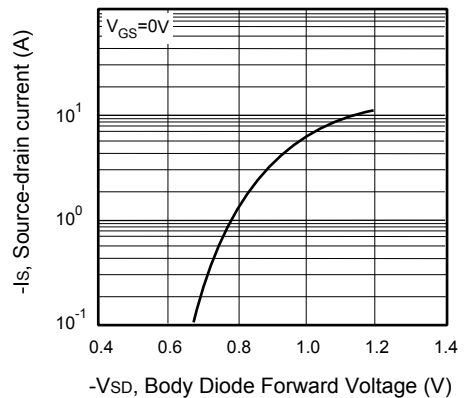


Figure 12. Body Diode Forward Voltage Variation with Source Current

N-CHANNEL

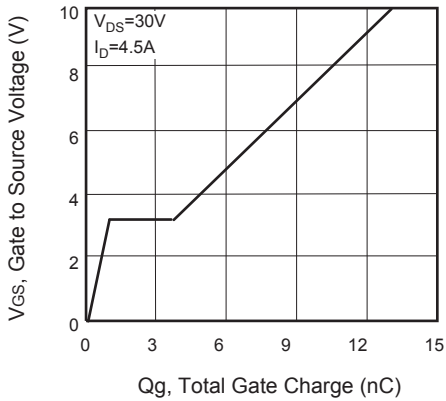


Figure 13. Gate Charge

P-CHANNEL

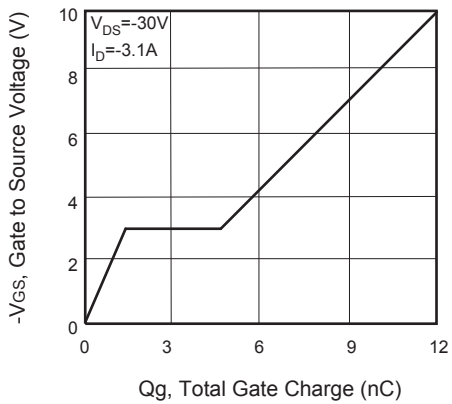


Figure 15. Gate Charge

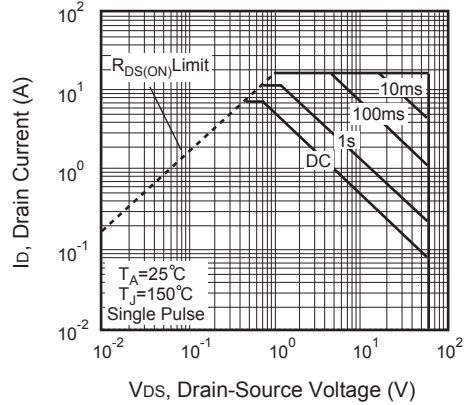


Figure 14. Maximum Safe Operating Area

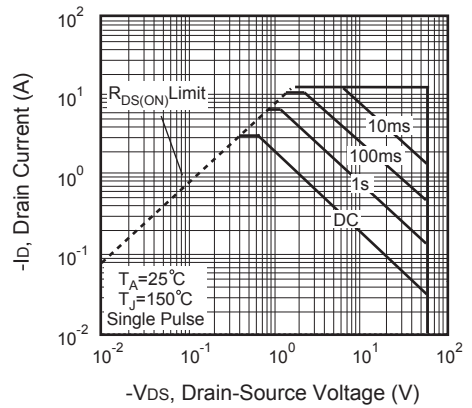


Figure 16. Maximum Safe Operating Area

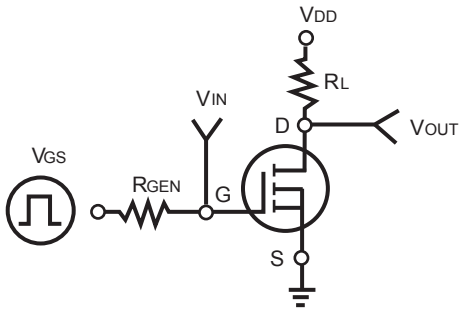


Figure 17. Switching Test Circuit

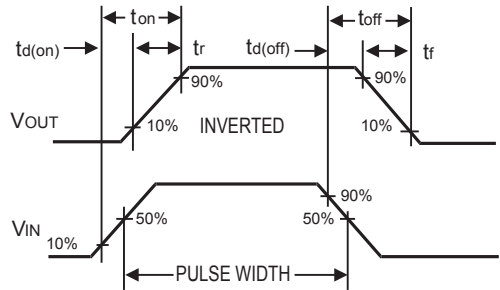


Figure 18. Switching Waveforms

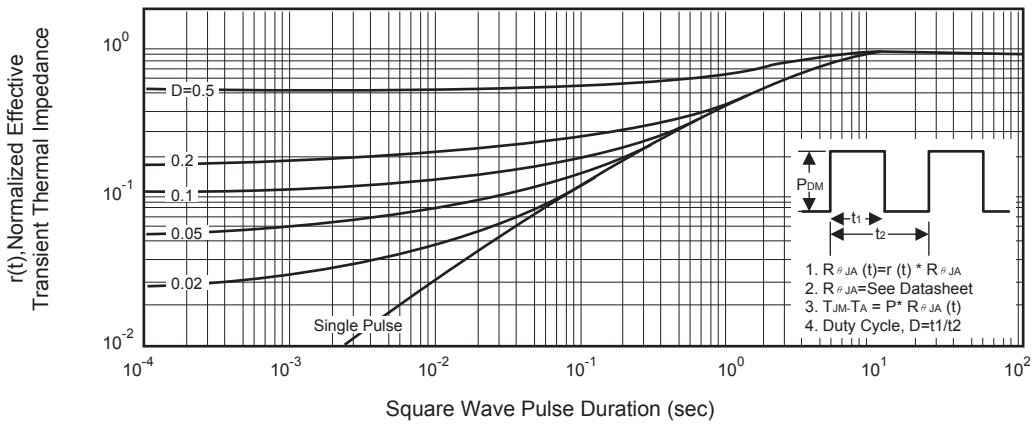


Figure 19. Normalized Thermal Transient Impedance Curve